HEWLETT-PACKARD COMPANY Intellectual Property Administration P. O. Box 272400 Fort Collins, Colorado 80527-2400

James R. Heath, et al.

Filed Herewith

Inventor(s):

Filing Date:

Application No.:

ATTORNEY DOCKET NO. 10981971-5

Confirmation No.:

Group Art Unit:

Examiner:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Title: Chemically Synthesized and Assembled Electronic Devices	
Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450 INFORMATION DISCLOSURE STATEMENT	
Sir:	
This Information Disclosure Statement is submitted:	
 (X) under 37 CFR 1.97(b), or (Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last) 	
 () under 37 CFR 1.97(c) together with either a: () Statement under 37 CFR 1.97(e), or () a \$180.00 fee under 37 CFR 1.17(p), or (After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs first) 	
 () under 37 CFR 1.97 (d) together with a: () Statement under 37 CFR 1.97(e)(1) or (2), and () a \$180.00 fee set forth in 37 CFR 1.17(p). (Filed after final action, a notice of allowance, on or before payment of the issue fee) 	
Please charge to Deposit Account 08-2025 the sum of <u>\$0.00</u> . At any time during the pendency of this application, please charge any fees required or credit any overpayment to Depose Account 08-2025 pursuant to 37 CFR 1.25.	ne sit
(X) Applicant(s) submit herewith Form PTO 1449 - Information Disclosure Statement together will any required copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may a duty to disclose in accordance with 37 CFR 1.56.	cn
() A concise explanation of the relevance of foreign language patents, foreign language publication and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by foreign patent office in a counterpart foreign application, an English language version of the sear report or action which indicates the degree of relevance found by the foreign office is listed on form PT 1449 and is enclosed herewith.	he a
It is requested that the information disclosed herein be made of record in this application.	
"Express Mail" label no. EL 968345551	

Telephone No.: (520) 399-3203

Attorney/Agent for Applicant(s)

26,857

Date: Oct. 31, 2003

James R. Heath, et al.

David W. Collins

Reg. No.

Rev 10/03 (IDSXML)

Typed Name: Myra Christ ck

Date of Deposit Oct. 30, 2003

I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Commissioner for Patents, Alexandria, VA 22313-1450.

Myra Christeck

Sheet 1 of 5

FORM PTO-1449					ATTY. DOCKET NO.	/	APPLICATION NO	CONFIRMATION	NO
LIST OF PATENTS AND PUBLICATIONS FOR					10981971-5				
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	╂	6,256,767	7/3/2001	Kue	kes et al.		ackground Refe		
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		5,475,341	12/12/95	Ree			ackground Refe		
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Sheet 3 of 5

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